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Lattice Engineering in MnO_2 via V^{5+} Doping for High-Performance Aqueous Te- MnO_2 Batteries

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Computational details

All spin-polarized density functional theory (DFT) computations were carried out using the Vienna Ab initio Simulation Package (VASP). The Perdew–Burke–Ernzerhof (PBE) functional within the generalized gradient approximation (GGA) was employed to represent the exchange–correlation interactions. Electron–ion interactions were treated using the projector augmented wave (PAW) method. A plane-wave energy cutoff of 450 eV was applied, and Brillouin zone sampling was performed with a 2×9×6 Monkhorst–Pack k-point grid. The convergence thresholds for the self-consistent field iterations were set to 10-5 eV for energy and 0.02 eV Å-1 for forces. To better describe the strongly correlated electrons, the DFT+U approach was applied with effective U values of 5.5 eV for Mn and 4.0 eV for V. Van der Waals interactions were incorporated via the DFT-D3 correction scheme. Structural models and calculation results were visualized using VESTA.

Preparation of α-MnO₂

A solution of KMnO₄ (0.395 g, 0.008 mol) in deionized water (35 mL) was mixed with MnSO₄·H₂O (0.169 g). The mixture was stirred magnetically for 30 minutes. It was then transferred into a Teflon-lined stainless-steel autoclave and heated at 160 °C for 12 hours. The resulting solid product was collected, washed repeatedly with deionized water and ethanol, and dried overnight at 60 °C.

Preparation of β-MnO₂

MnSO₄·H₂O (1.352 g, 0.008 mol) and (NH₄)₂S₂O₈ (1.826 g, 0.008 mol) were dissolved in deionized water (40 mL) under magnetic stirring. After 30 minutes, the mixture was transferred into a Teflon-lined stainless-steel autoclave and heated at 140 °C for 12 hours. The solid product was washed several times with deionized water and ethanol, and then dried at 60 °C overnight.

Preparation of γ-MnO₂

MnSO₄ (4.50 mmol) was dissolved in deionized water, followed by the addition of an aqueous (NH₄)₂S₂O₈ solution (4.93 mmol). The mixture was placed in a Teflon-lined stainless-steel autoclave and heated at 90 °C for 24 hours. The solid product was washed multiple times with deionized water and ethanol, and finally dried at 60 °C overnight.

Synthesis of C@Te composite

100 mg of tellurium powder was thoroughly mixed with 50 mg of Ketjen black, then transferred to a tube furnace and heated to 500 °C at a rate of 2 °C min⁻¹ under an argon atmosphere, followed by maintaining at that temperature for 5 h.

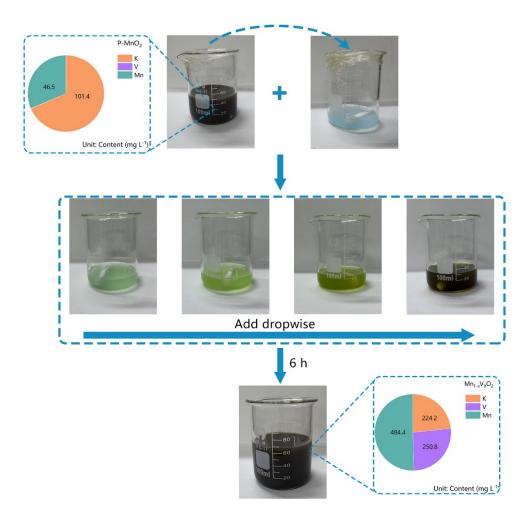


Figure S1. Schematic diagram of the reaction process, showing the elemental composition and content before and after the reaction.

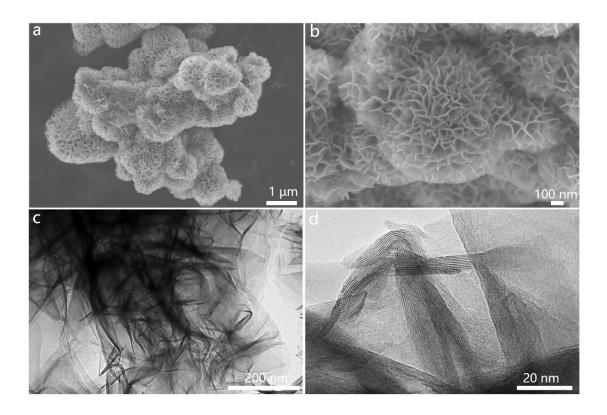


Figure S2. (a, b) SEM and TEM (c, d) images of P-MnO2 at different magnifications.

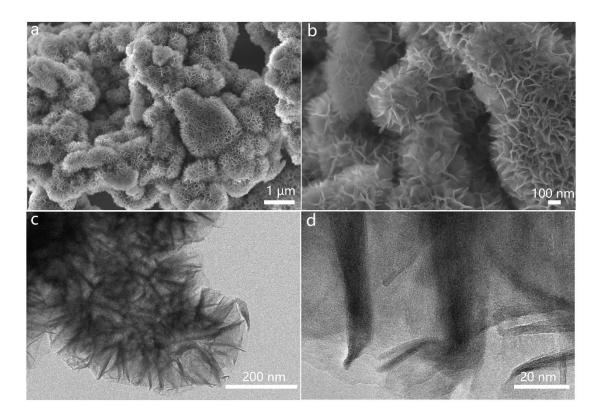


Figure S3. (a, b) SEM and TEM (c, d) images of $Mn_{1\text{-x}}V_xO_2$ at different magnifications.

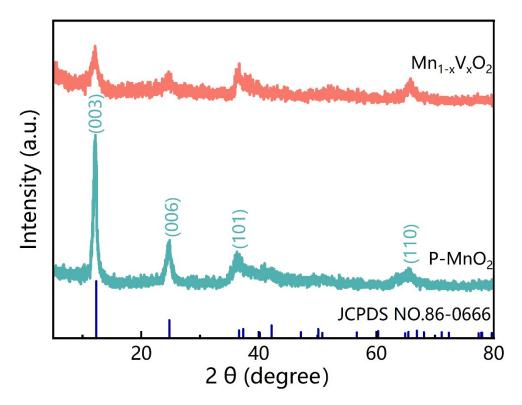


Figure S4. XRD pattern of the samples.

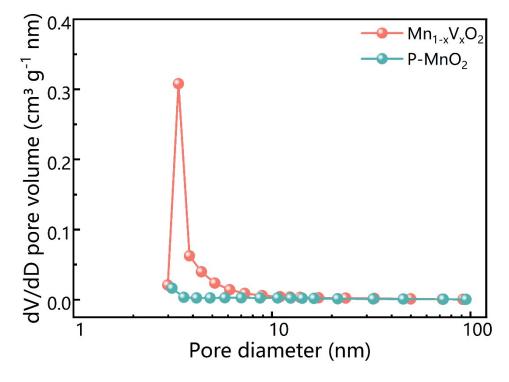


Figure S5. Pore size distribution curves of the samples.

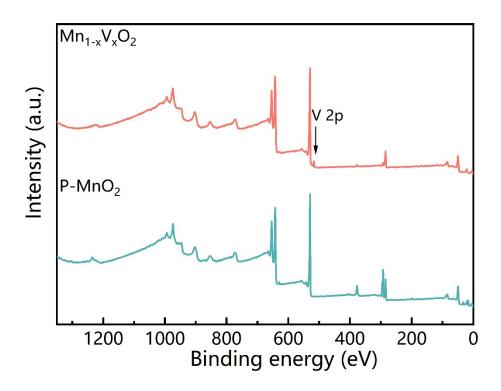


Figure S6. XPS survey spectrum of the samples.

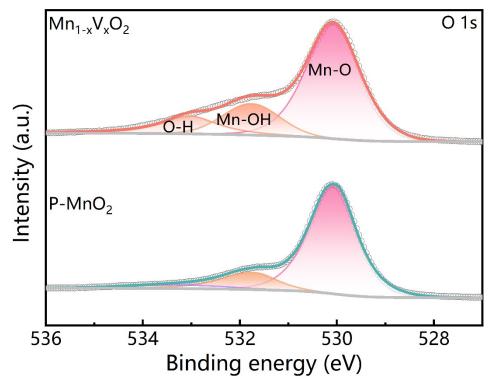


Figure S7. High-resolution XPS spectrum of O 1s.

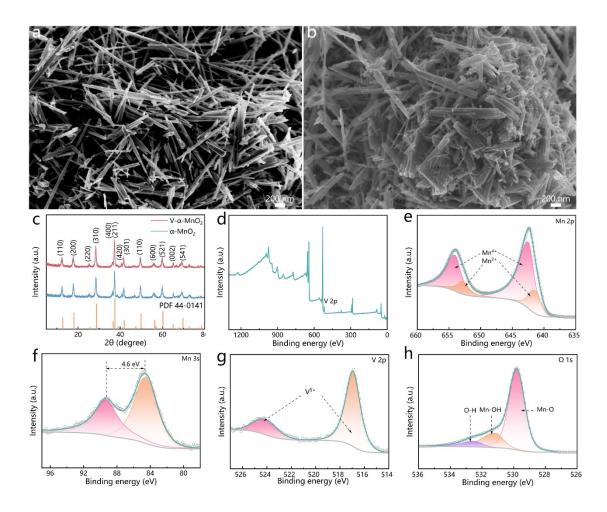


Figure S8. Morphological and structural characterization: (a) Pristine α -MnO₂ before reaction, (b) V-doped α -MnO₂, (c) XRD patterns, (d) XPS survey spectrum of V-doped α -MnO₂, and (e-h) high-resolution XPS spectra of (e) Mn 2p, (f) Mn 3s, (g) V 2p, and (h) O 1s.

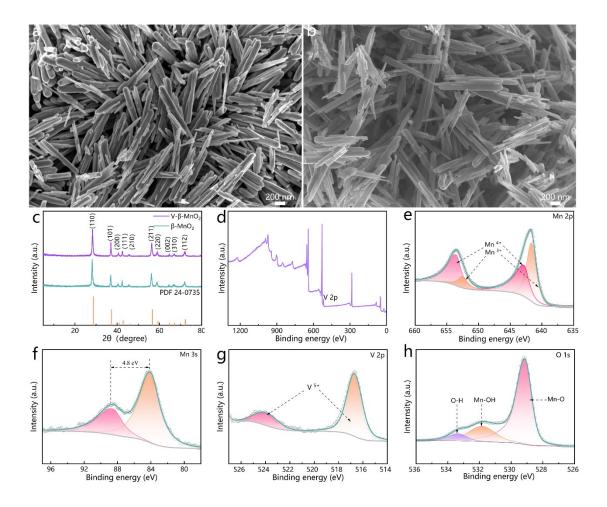


Figure S9. Morphological and structural characterization: (a) Pristine β -MnO₂ before reaction, (b) V-doped β -MnO₂, (c) XRD patterns, (d) XPS survey spectrum of V-doped β -MnO₂, and (e-h) high-resolution XPS spectra of (e) Mn 2p, (f) Mn 3s, (g) V 2p, and (h) O 1s.

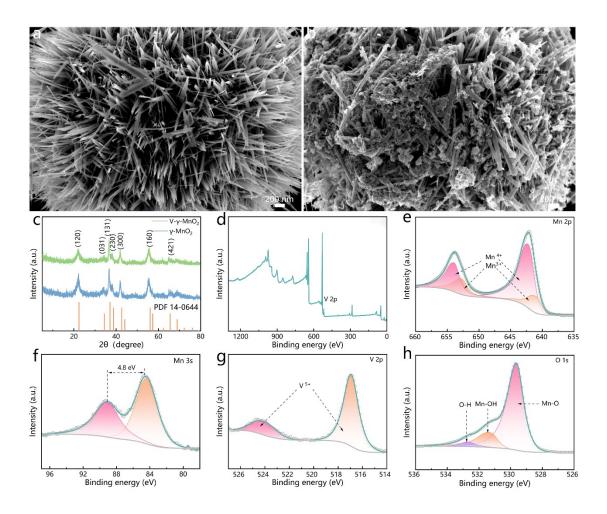


Figure S10. Morphological and structural characterization: (a) Pristine γ-MnO₂ before reaction, (b) V-doped γ-MnO₂, (c) XRD patterns, (d) XPS survey spectrum of V-doped γ-MnO₂, and (e-h) high-resolution XPS spectra of (e) Mn 2p, (f) Mn 3s, (g) V 2p, and (h) O 1s.

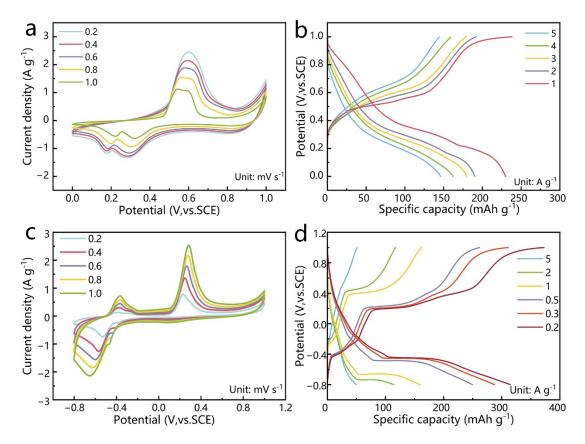


Figure S11. Electrochemical performance of the $Mn_{1-x}V_xO_2$ and C@Te in three-electrode configuration. (a) CV curves and (b) GCD curves of the $Mn_{1-x}V_xO_2$; (c) CV curves and (d) GCD curves of the C@Te.

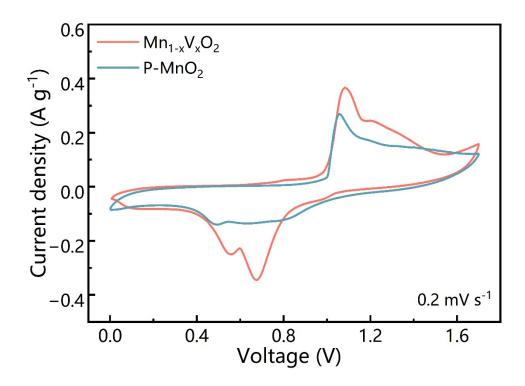


Figure S12. CV curves of the samples.

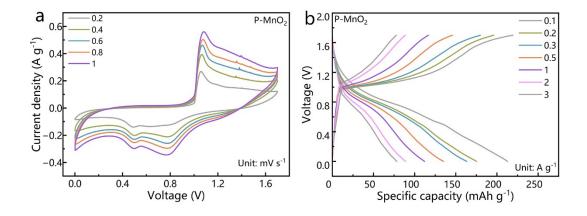


Figure S13. CV and GCD curves of the P-MnO₂.

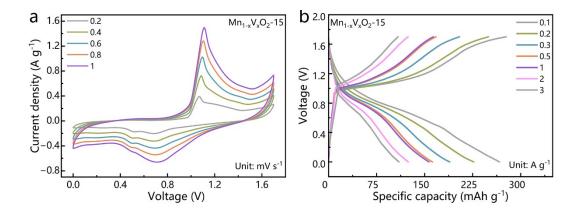


Figure S14. CV and GCD curves of the samples obtained at the low content of VOSO₄ (15 mg).

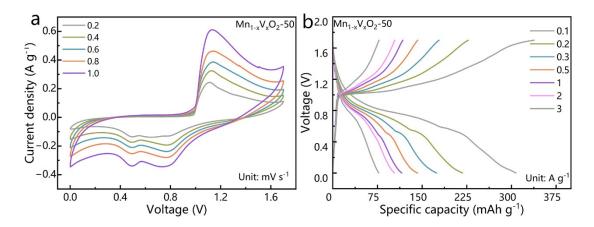


Figure S15. CV and GCD curves of the samples obtained at the high content of VOSO₄ (50 mg).

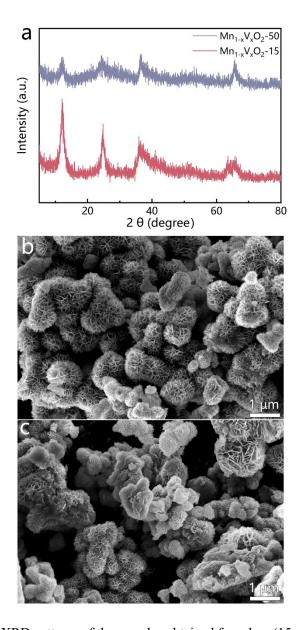


Figure S16. (a) XRD patterns of the samples obtained from low (15 mg) and high (50 mg) VOSO₄ content. SEM image of the (b) low (15 mg) and (c) high (50 mg) VOSO₄ content.

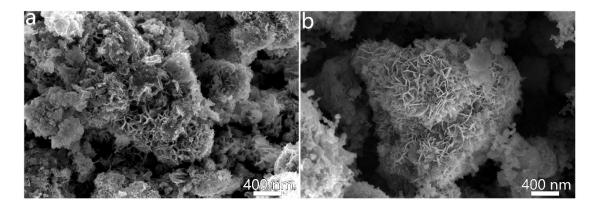


Figure S17. SEM images after cycling test, (a) P-MnO $_2$ and (b) Mn $_{1-x}V_xO_2$.

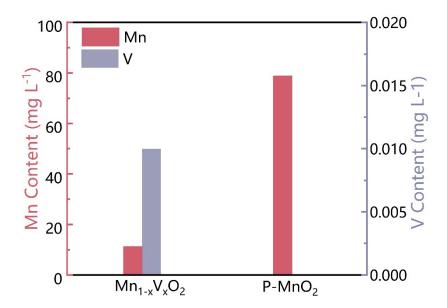


Figure S18. The content of Mn and V in the electrolyte after the cycle stability test.

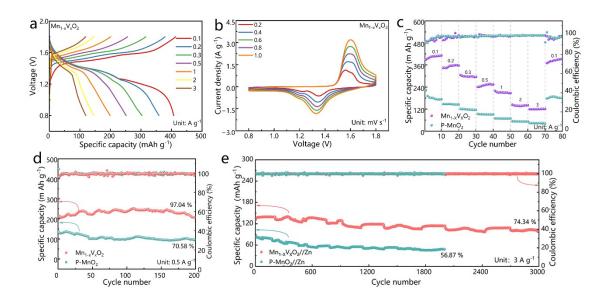


Figure S19. Electrochemical performance of the Zn-MnO₂ battery. (a, b) GCD and CV curves of the $Mn_{1-x}V_xO_2$ cathode. (c) Rate capability. (d, e) Cycling stability at 0.5 and 3 A g⁻¹, respectively.

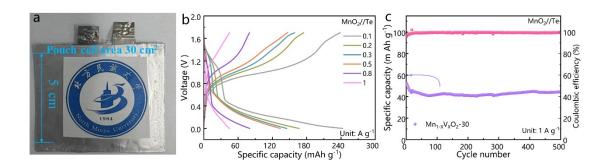


Figure 20. Electrochemical performance of pouch cell: (a) Photograph, (b) GCD profiles, and (c) cycling stability at 1 A g⁻¹.

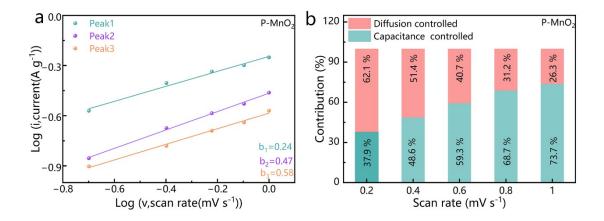


Figure S21. (a) Relationship between log(i) and log(v). (b) Contribution ratio of capacitive and diffusion-controlled capacities at different scan rates for P-MnO₂.

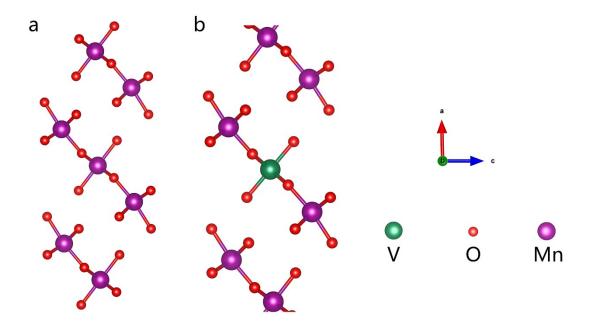


Figure S22. Crystal structures of (a) P-MnO₂ and (b)V-doped MnO₂.

Table S1. Refined fractional atomic coordinates and their estimated standard deviations.

sample	P-MnO2			$Mn_{1-x}V_xO_2$		
atom	X	у	Z	X	у	z
Mn0	0.14624	1/2	0.01621	0.15931	1/2	0.02027
Mn1	0	0	1/2	0	0	1/2
O2	0.04354	1/2	0.17379	0.06114	1/2	0.30635
О3	0.12784	0	0.42584	0.10068	0	0.79902
O4	0.31993	0	0.55043	0.22602	0	0.21585
V				0.15931	1/2	0.02027
V				0	0	1/2

 $\textbf{Table S2.} \ \, \text{Comparison of the electrochemical performance of the } \ \, Mn_{1\text{-}x}V_xO_2 \ \, \text{with recently reported}$ cathodes.

Sample	Specific	Rate capacity	Capacity	Reference
	capacity	retention	retention	
MnO ₂ -	306 mAh g ⁻¹ at	105 mAh g ⁻¹ at	100% at 1.0 A g ⁻¹ (after	
BET//Zn	0.1 A g ⁻¹	5.0 A g ⁻¹	700 cycles);	[1]
			95% at 5.0 A g ⁻¹ (after	
			8000 cycles)	
CMC-	324 mAh g ⁻¹ at	237 mAh g ⁻¹ at	100% at 0.5 A g ⁻¹ (after	
$MnO_2//Zn$	0.5A g ⁻¹	3 A g ⁻¹	200 cycles)	[2]
			86.2% at 1.5 A g ⁻¹ (after	
			1000 cycles)	
NHMO	287.9 mAh g ⁻¹	99.4mAh g ⁻¹ at	96.5% at 0.2A g ⁻¹ (after	
//Zn	at 0.1 A g ⁻¹	6 A g ⁻¹	500 cycles)	[3]
			90% at 6 A g ⁻¹ (after	
			13000 cycles)	
Н-	260 mAh g ⁻¹ at	97 mAh g ⁻¹ at	98% at 0.4 A g ⁻¹ (after 100	
MnO ₂ //Zn	0.2 A g ⁻¹	3.8 A g ⁻¹	cycles)	[4]
			95% at 3.8 A g ⁻¹ (after	
			5000 cycles)	
Ca/N-	325 mAh g ⁻¹ at	64.2 mAh g ⁻¹ at	70% at 1 A g ⁻¹ (after 200	
MnO ₂ //Zn	0.3A g ⁻¹	3 A g ⁻¹	cycles)	[5]

			70.4% at 3 A g ⁻¹ (after	
			1000 cycles)	
MnO ₂ //Te	177 mAh g-1 at	62 mAh g ⁻¹ at 5	76.5% at 1 A g ⁻¹ (after	[6]
	0.1 A g ⁻¹	A g ⁻¹	5000 cycles)	
MnO ₂ @AE	268 mAh g ⁻¹ at	84 mAh g ⁻¹ at 5	100% at 0.5 A g^{-1} (after	
PA	0.2 A g ⁻¹	A g ⁻¹	200 cycles)	[7]
			97% at 1 A g ⁻¹ (after 1700	
			cycles)	
T-	398 mAh g ⁻¹ at	90 mAh g ⁻¹ at	100% at 1.0 A g ⁻¹ (after	[8]
MnO ₂ //Zn	0.2 A g ⁻¹	1.5 A g ⁻¹	1200 cycles)	
δ-MnO ₂ @2-	309.5 mAh g ⁻¹	137.6mAh g ⁻¹	80% at 1.0A g ⁻¹ (after	[9]
ML	at 0.1 A g ⁻¹	at 1.0A g ⁻¹	1350 cycles)	
Bi-	363 mAh g ⁻¹ at	103 mAh g ⁻¹ at	100% at $0.1~A~g^{-1}$ (after	
MnO ₂ //Zn	0.1 A g ⁻¹	3.0 A g ⁻¹	100 cycles)	[10]
			93% at 1.0 A g ⁻¹ (after	
			10000 cycles)	
$MnO_2(O_d)$	330.9 mAh g ⁻¹	225 mAh g ⁻¹ at	88.9% at 1 A g ⁻¹ (after 800	[11]
//Zn	at 0.1 A g ⁻¹	2.0 A g ⁻¹	cycles)	
WO3/WC	69 mAh g ⁻¹	21 mAh g ⁻¹	100% at 1.0 A g ⁻¹ (after	[12]
MnO ₂ /graph	at 0.1 A g ⁻¹	at5.0 A g ⁻¹	10000 cycles)	
ite				
NHVO@Ti ₃	498.4 mAh g ⁻¹	98.2 mAh g ⁻¹ at	92.1% at 2.0 A g ⁻¹ (after	[13]

C ₂ T _x //ZnMn	at 0.1 A g ⁻¹	2.0 A g ⁻¹	6000 cycles)	
$_2\mathrm{O}_4$				
$p ext{-}MoSe_2 Z$	84.8 mAh g ⁻¹	28.1 mAh g ⁻¹	71.9 % at 0.015A g ⁻¹ (after	
nxNVPF	at 0.04 A g ⁻¹	at 0.04 A g ⁻¹	160 cycles)	[14]
			79.9% at 0.2A g ⁻¹ (after	
			5000 cycles)	
AgNWA@	240.6 mAh g ⁻¹	90.0 mAh g ⁻¹ at	94.4% at 5.0A g ⁻¹ (after	[15]
$Zn//\alpha$ -	at 0.1 A g ⁻¹	10.0 A g ⁻¹	1500 cycles)	
MnO2				
Se-	368 mAh g ⁻¹ at	125 mAh g ⁻¹ at	100% at 0.1A g ⁻¹ (after	
MnO ₂ //Zn	0.1 A g ⁻¹	0.1 A g ⁻¹	100 cycles)	[16]
			71% at 3 A g ⁻¹ (after 5000	
			cycles)	
K-	285 mAh g ⁻¹ at	211.8 mAh g ⁻¹	80.1% at 1 C (after 100	[17]
MnO ₂ //Zn	0.2 C	at 4 C	cycles)	
Mo-	270 mAh g ⁻¹ at	90 mAh g ⁻¹ at 2	92.6% at 0.1A g ⁻¹ (after	
MnO ₂ //Zn	0.1 A g ⁻¹	A g ⁻¹	100 cycles)	[18]
			80.1% at 1 A g ⁻¹ (after	
			16000cycles)	
Ag-	306 mAh g ⁻¹ at	160 mAh g ⁻¹ at	75% at 0.1 A g ⁻¹ (after 75	
MnO ₂ //Zn	0.1 A g ⁻¹	2 A g ⁻¹	cycles)	[19]
			50% at 1 A g ⁻¹ (after 800	

cycles) 600 mAh g⁻¹ at 260 mAh g⁻¹ at 77.2% at 1C (after 700 Mg-1 C 5 C $MnO_2//Zn$ cycles) [20] 36% at 5C (after 640 cycles) Mn_{1} 323.7mAh 120.5mAh g⁻¹ 92.93% at 0.5 A g⁻¹ (after This work at 0.1 A g⁻¹ at 3A g⁻¹ 1000 cycles) $_{x}V_{x}O_{2}//Te@$ C 94.08% at 0.5 A g⁻¹ (after 5000 cycles)

Mn₁. 406.9 mAh g⁻¹ 119.2mAh g⁻¹ 97.04% at 0.5 A g⁻¹ (after This work $_xV_xO_2$ //Zn at 0.1 A g⁻¹ at 3A g⁻¹ 200 cycles) $74.34\% \text{ at 3 A g}^{-1} \text{ (after }$ 3000 cycles)

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